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Form 1449*	Atty. Docket No.: 303.326US1	Serial No. 08/903,486
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
	Filing Date: July 29, 1997	Group: 1104 2811

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**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
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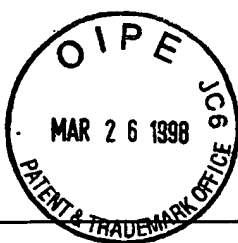
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